

# Graphene photosensors

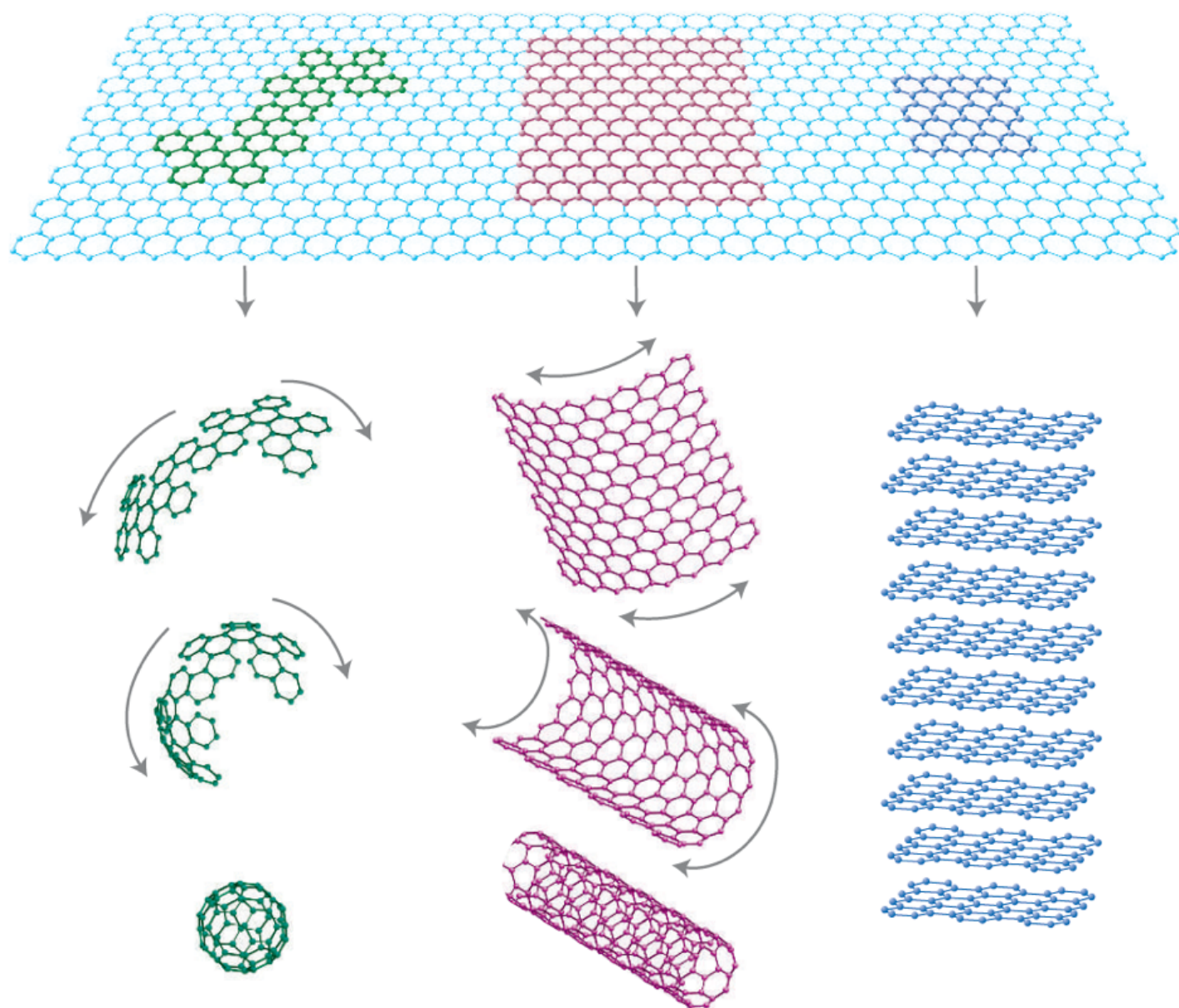
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for the IFAE-graphene:

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# Graphene



- Graphene is a flat monolayer of carbon atoms packed into a 2D layout. (2D crystal).
- 2D crystals were believed not to exist until the discovery of Graphene crystals in 2004.
- Actually Graphene is a very high quality crystal.
- But, not the only one known as of today!





# Why Graphene?



- The single layer and bi-layer Graphene behaves like a zero-gap semiconductor with only one electron type and one hole type.
- The electronic structure evolves fast when adding layers with different electronics and optical properties.
- The graphene can be doped altering the electronic properties of the material.
- Electron and holes has a large mobility:  $15000 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$  with large concentrations  $10^{13} \text{ cm}^{-2}$
- Electrons interacting with the graphene lattice produce charge carriers wich are basically massless moving at the speed of light. (A charged neutrino!!!!)

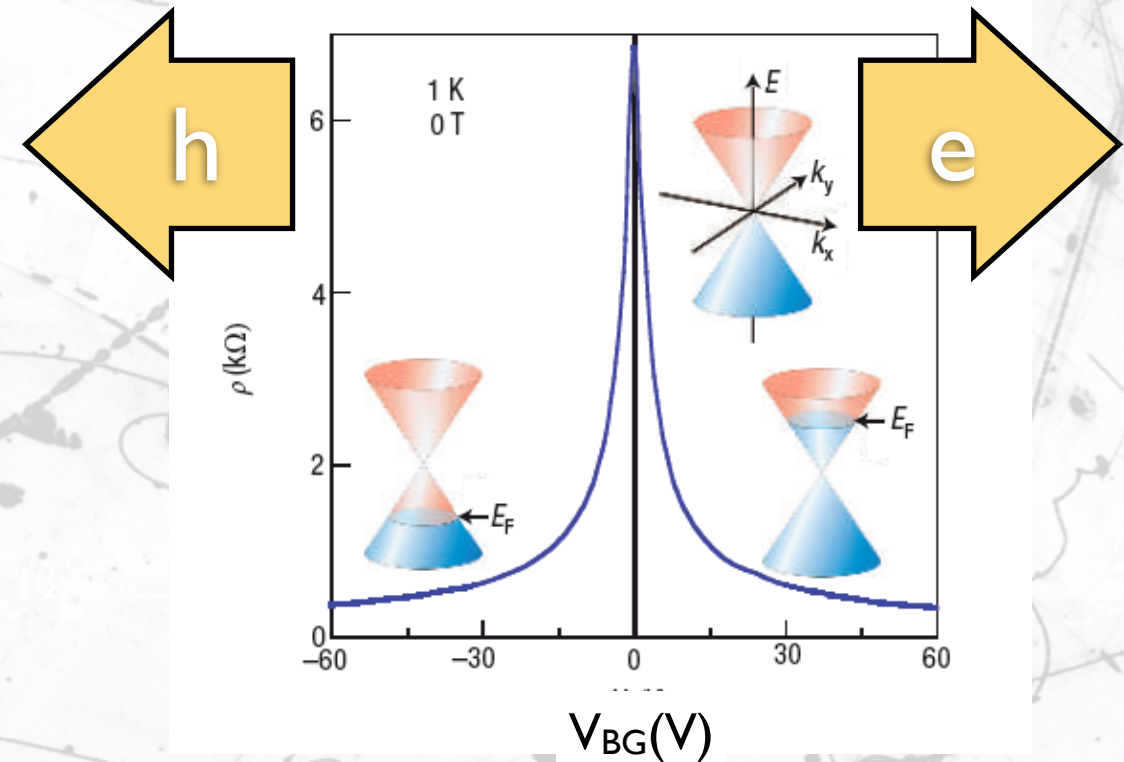
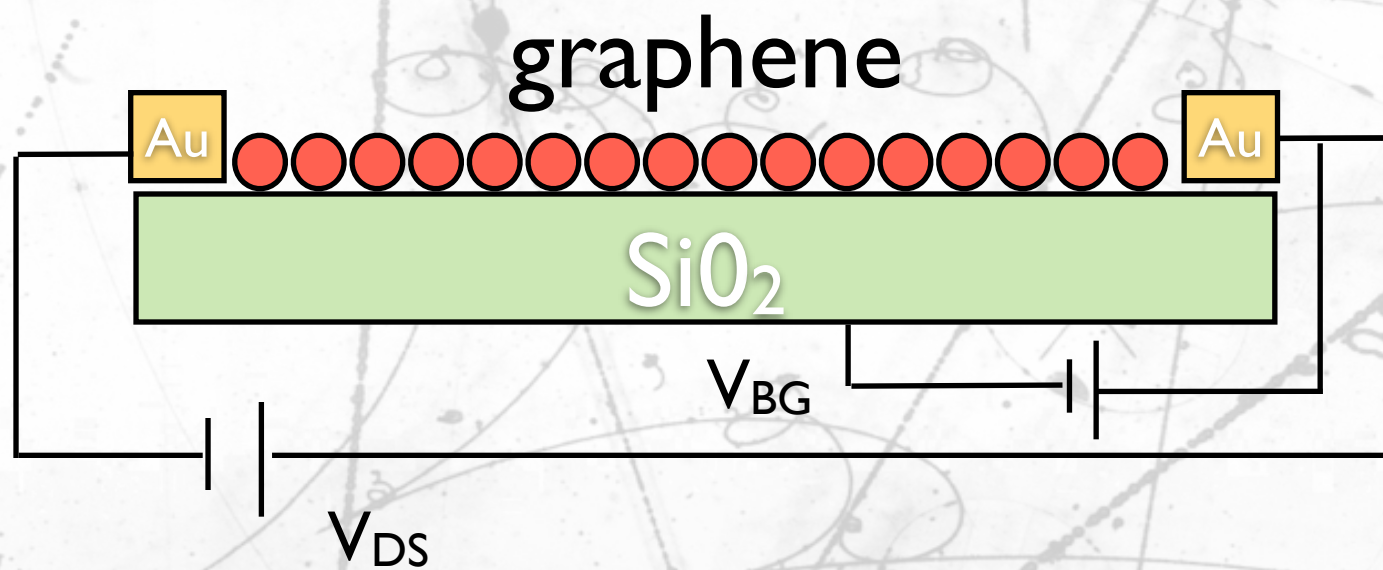
$$E_{\pm}(k) \approx \hbar v_F |k - K|$$

Graphene might become a laboratory to study high precision QED





# Electric properties



- Let's deposit a layer of Graphene on a piece of semiconductor SiO<sub>2</sub>
- Bias the SiO<sub>2</sub> with voltage V<sub>BG</sub>.
- Check the graphene resistance.

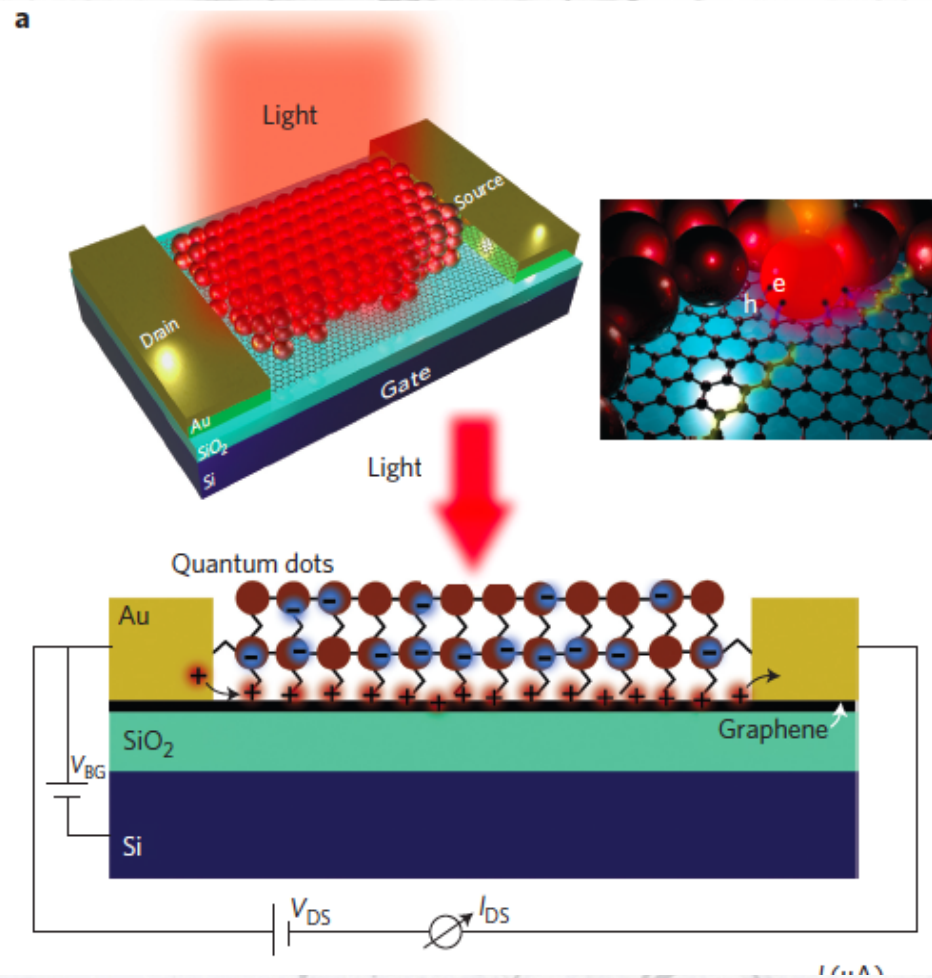
- V<sub>BG</sub> changes the level of occupancy and allows for electron or hole conduction by changing the Fermi Level.
- The maximum resistance is the so-called Dirac Point.

E(k) is the energy as function of the particle momentum.

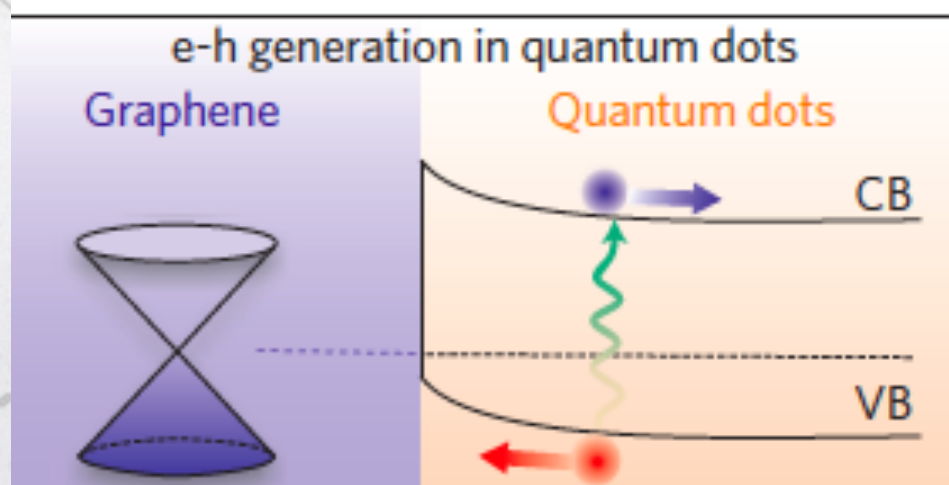




# As photosensors

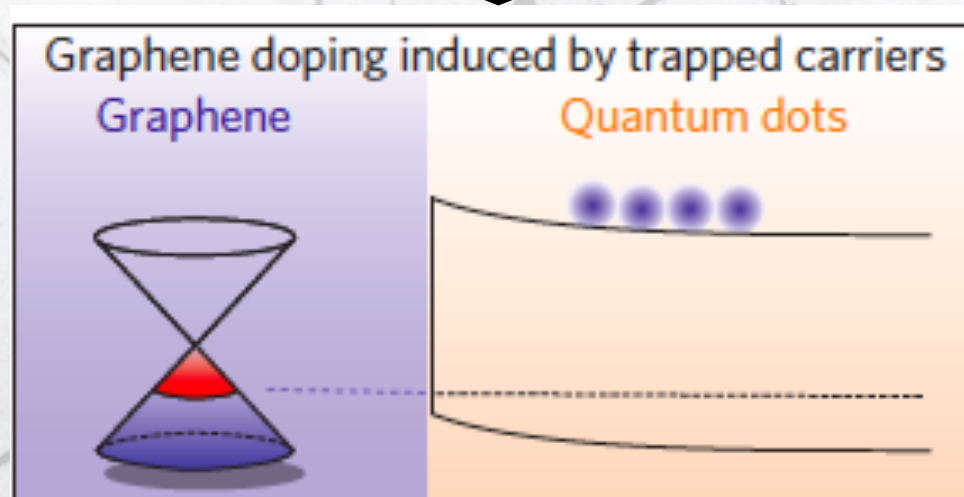
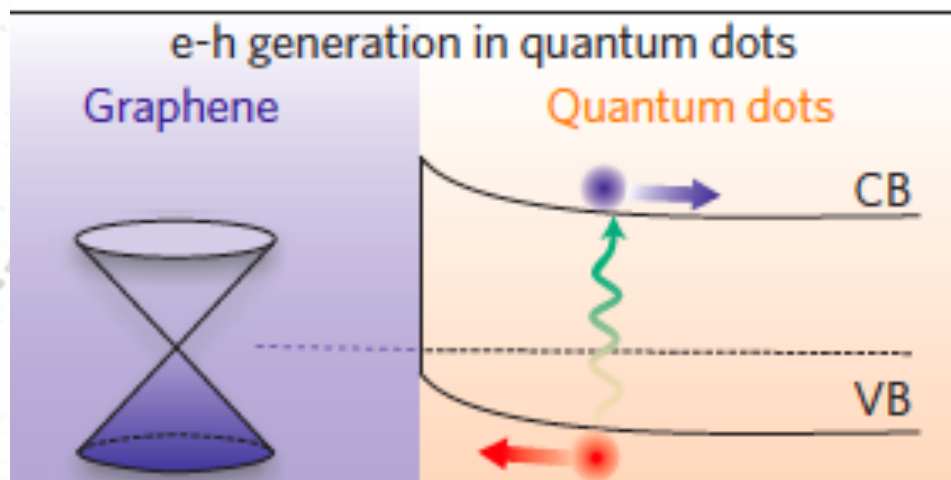


- Graphene alone is not expected to show photocurrent because of the fast recombination of the charge carriers.
- Now let's dope the graphene with quantum dots: nano particles of PbS with 900 to 1500 nm.
- First effect is that the Dirac point shifts from  $\sim 50$  to  $\sim 120$  V:
- there is an electric field induced in the surface between Si and graphene that is compensated by  $V_{BG}$  such that it equals the new Dirac value ( $V_D$ )





# As photosensors

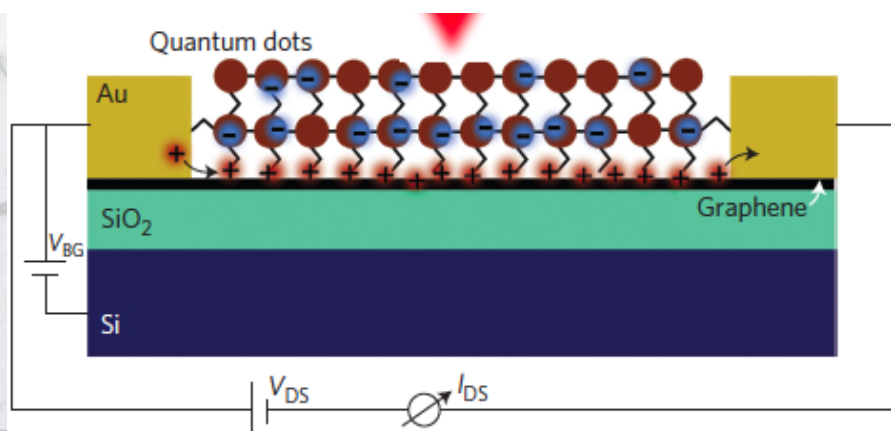
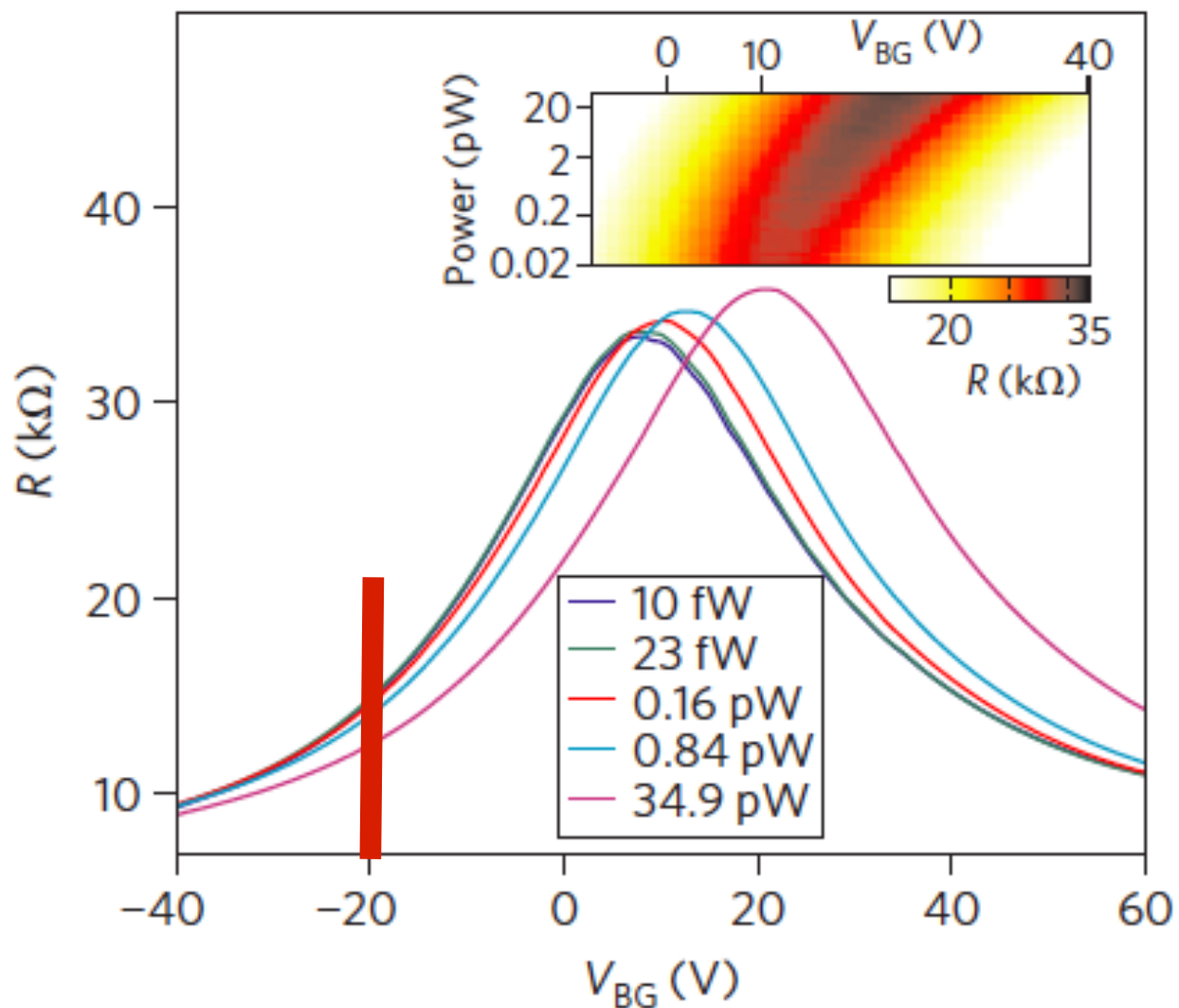
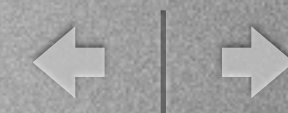


- Light is absorbed by the quantum dots:
- holes are transferred to the graphene.
- electrons are trapped in the quantum dots for some time.
- The Dirac point voltage is then shifted (different surface E field).
- If the  $V_g$  is not changed, the resistance of the graphene changes.!





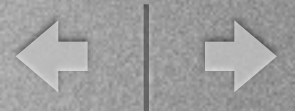
# As photosensors



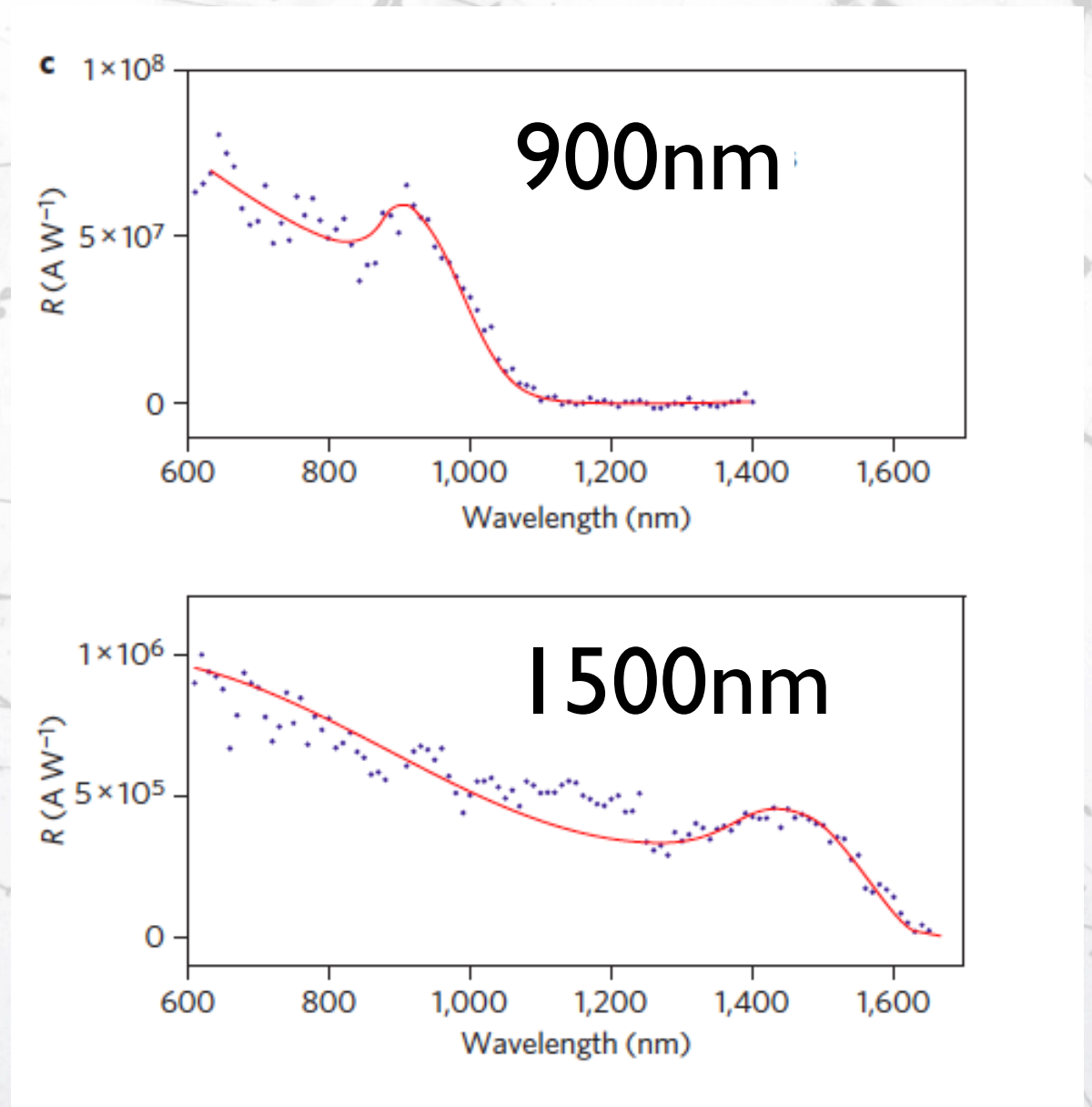
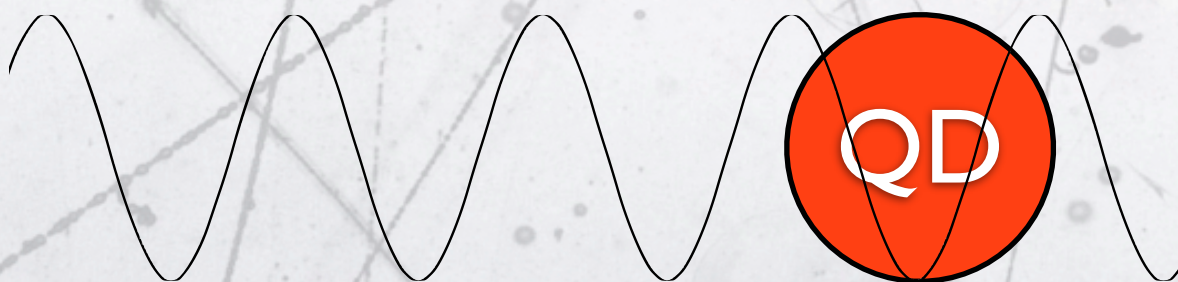
- The Dirac point shifts in the presence of light.
- Maintaining the  $V_{BG}$  we should see a change in the resistance of the graphene.
- This is measured as a change in the current over the  $V_{ds}$ .
- For the full time the electron remains in the quatum-dot ( $\sim 10$ ms) the resistance is changed.
- $\text{Gain} = (I_{\text{light}} - I_{\text{dark}}) \Delta t$



# Quantum dots

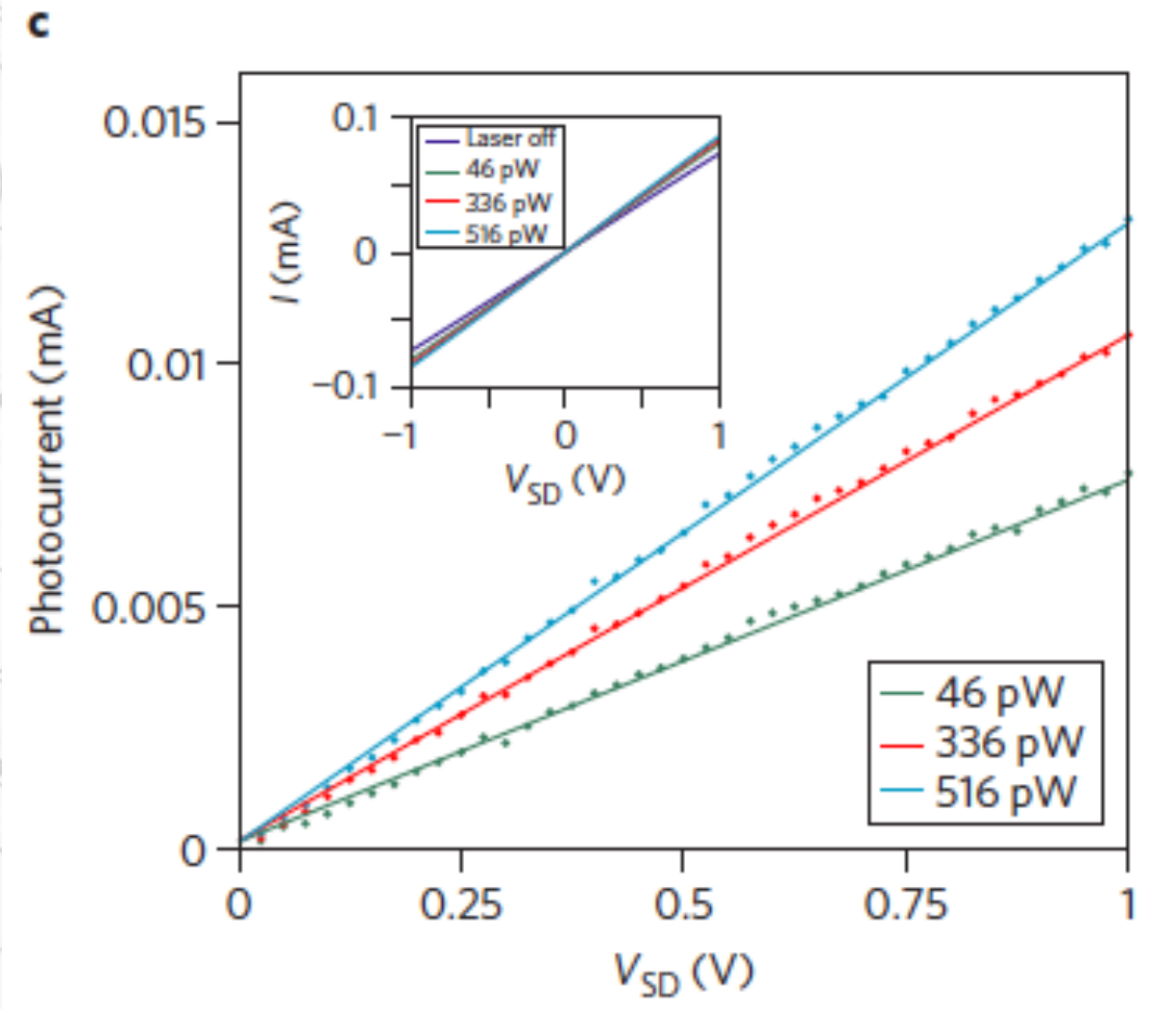
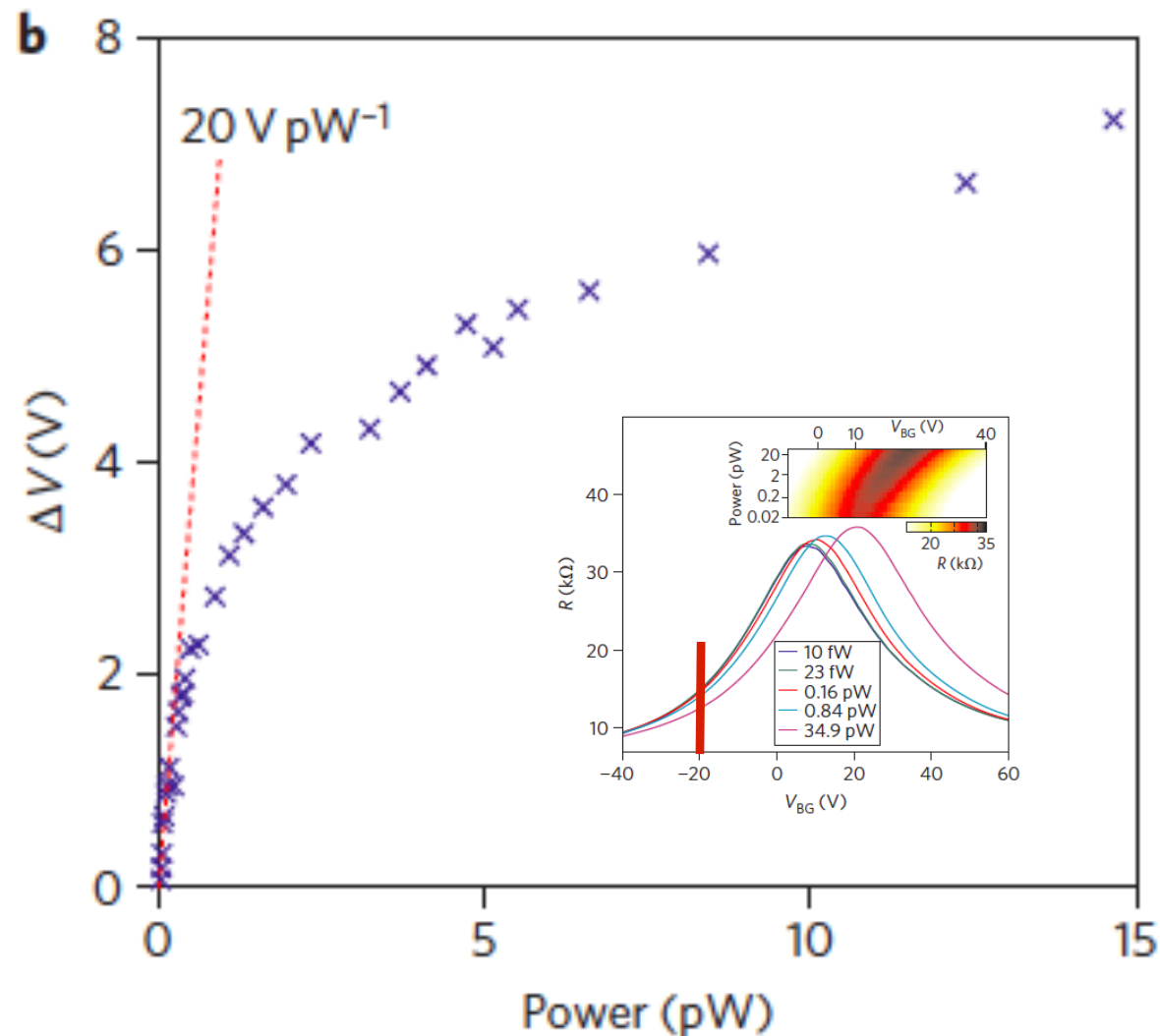
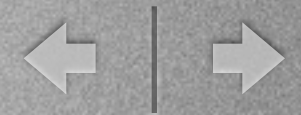


- Quantum dots has large absorption probability for photons with  $\lambda \sim$  diameter...
- and below, but it shows a clear cut off for lower energies.





# As photosensors



For low power, the response is linear with light intensity.

The response is typical of a resistance.



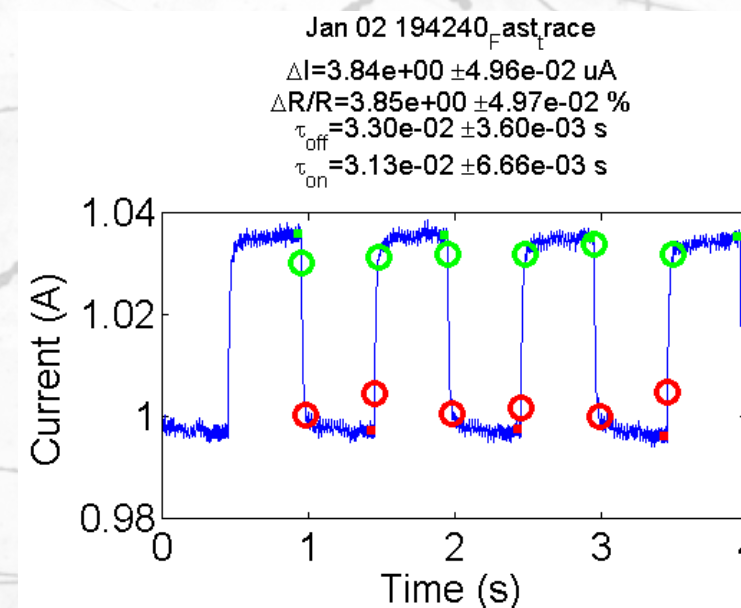
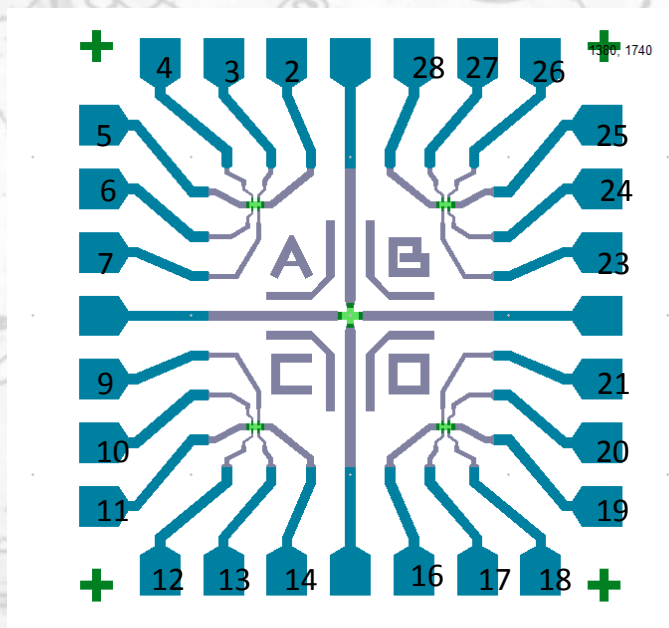


- In October IFAE started a collaboration with the ICFO to develop a readout for a highly integrated pixelized graphene photosensor.
- The purpose of the IFAE is twofold:
  - characterise from the electronics point of view the device (noise, ... )
  - develop a low consumption readout system that can be integrated in an ASIC.
- The group got support by the IFAE Severo Ochoa.

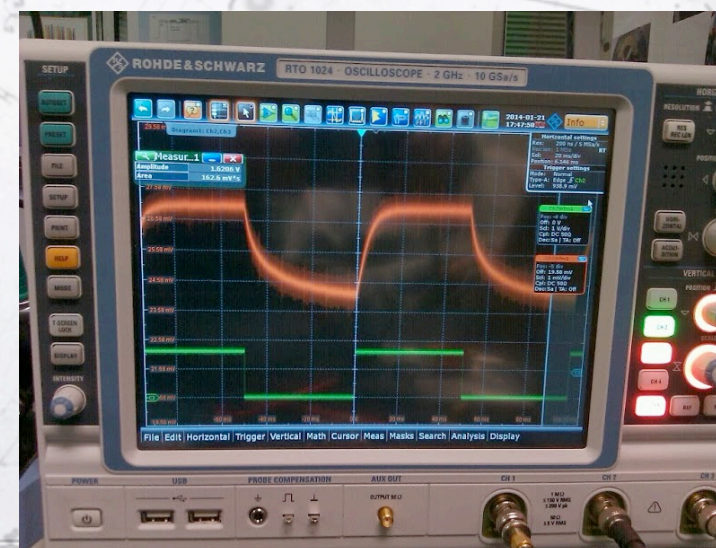
IFAE motivation to join effort is explained later



- ICFO provided 4 graphene sensors doped with 985 nm in January.

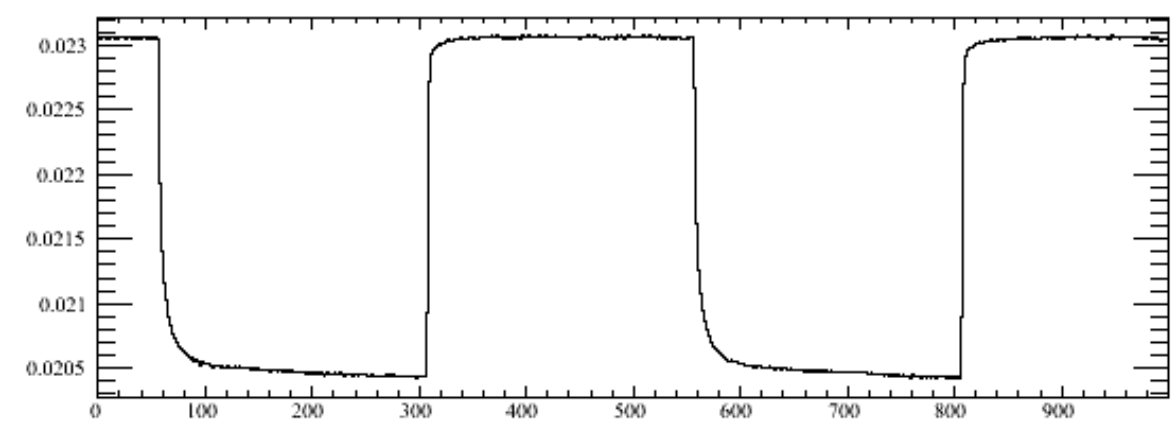
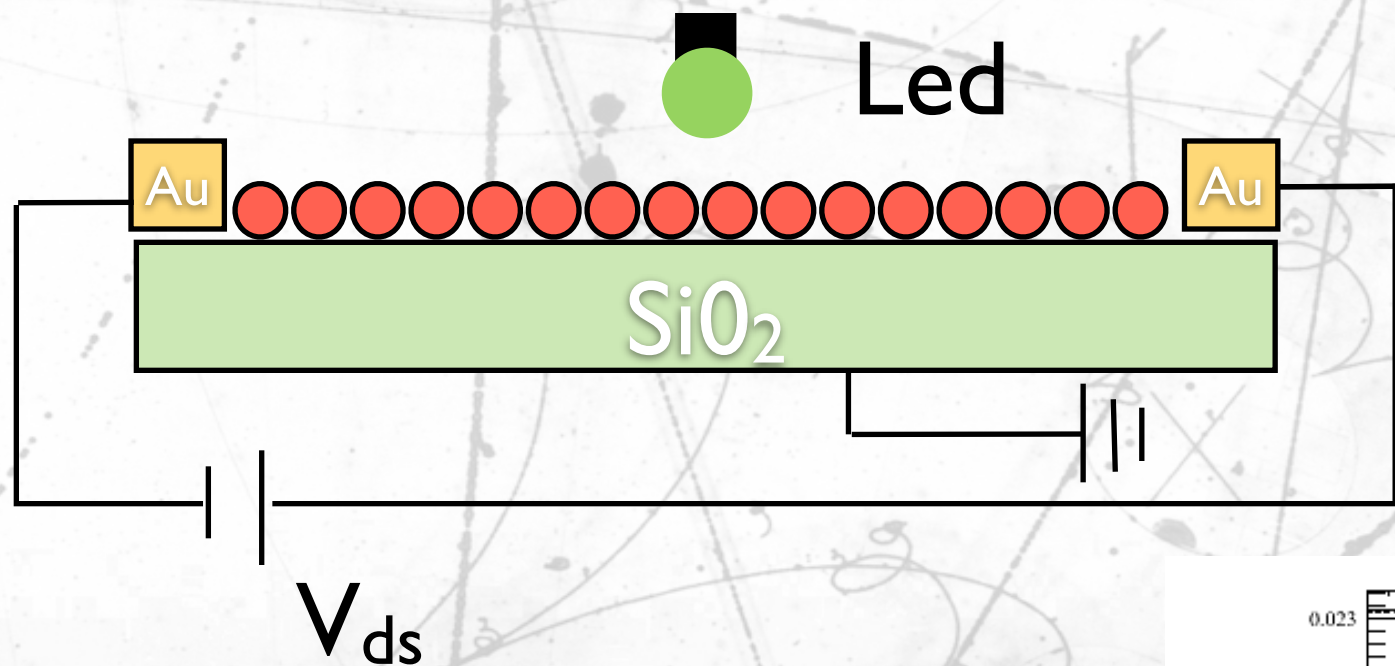


- We saw the first response at the end of January.

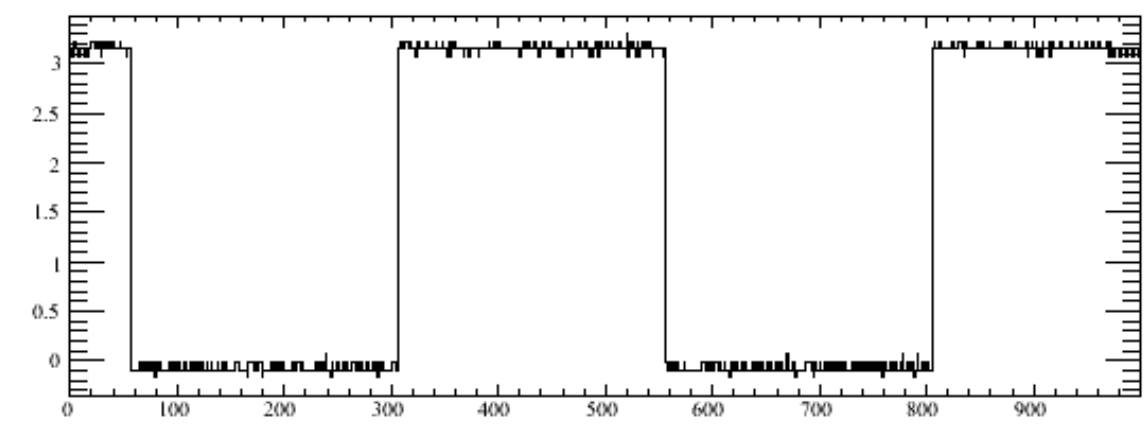




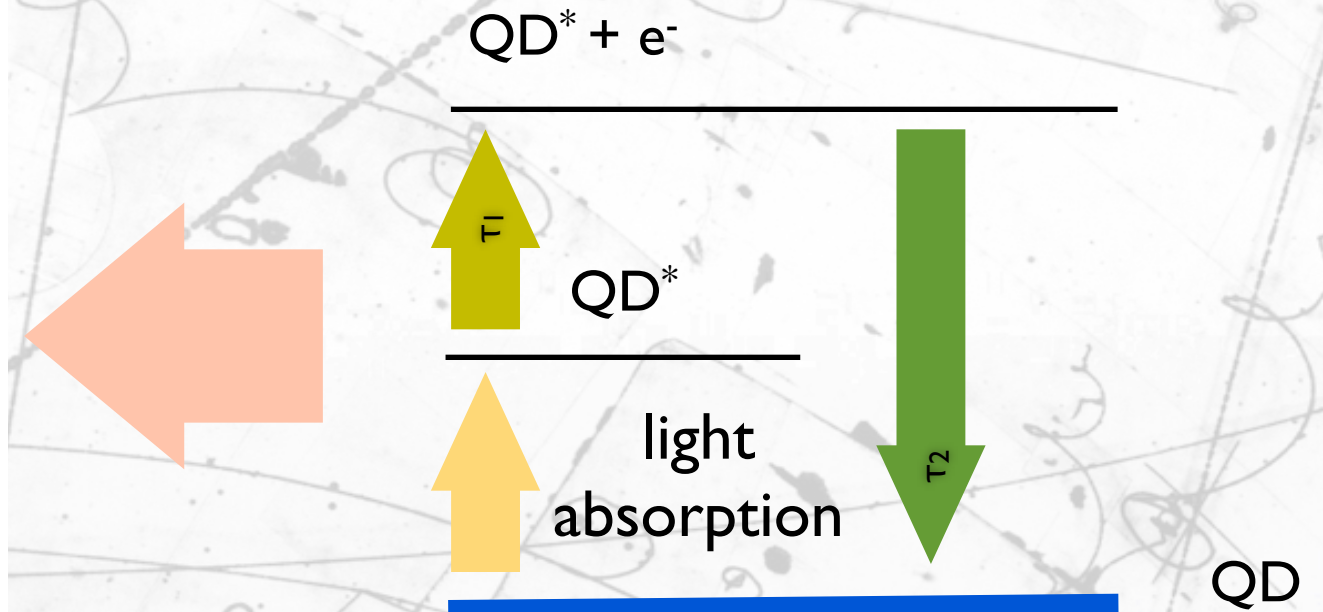
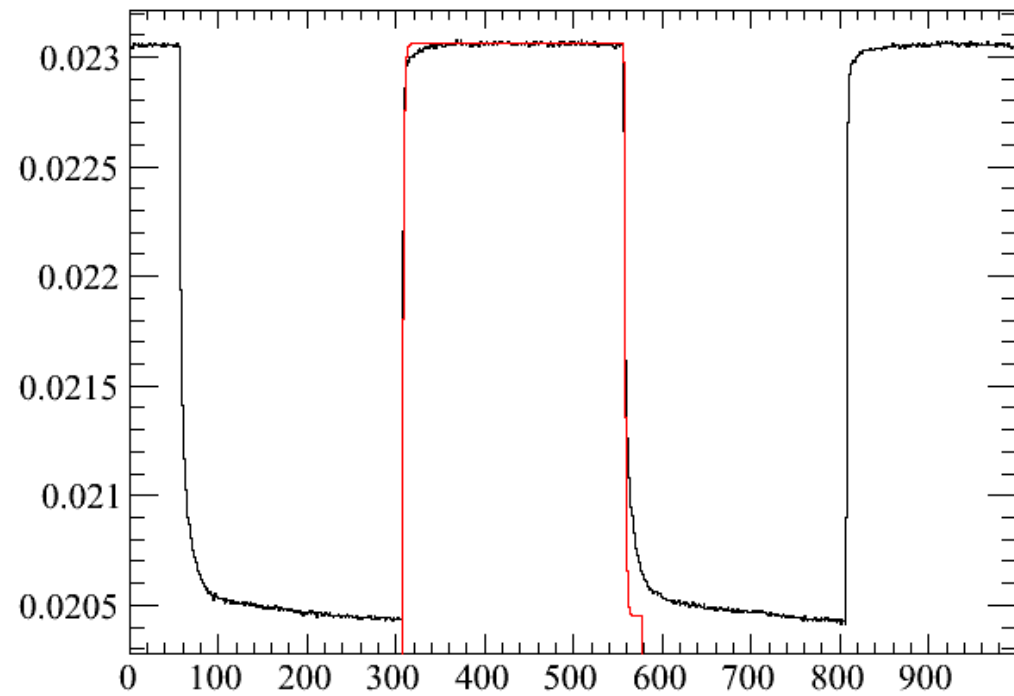
# Graphene @ IFAE



Led pulse

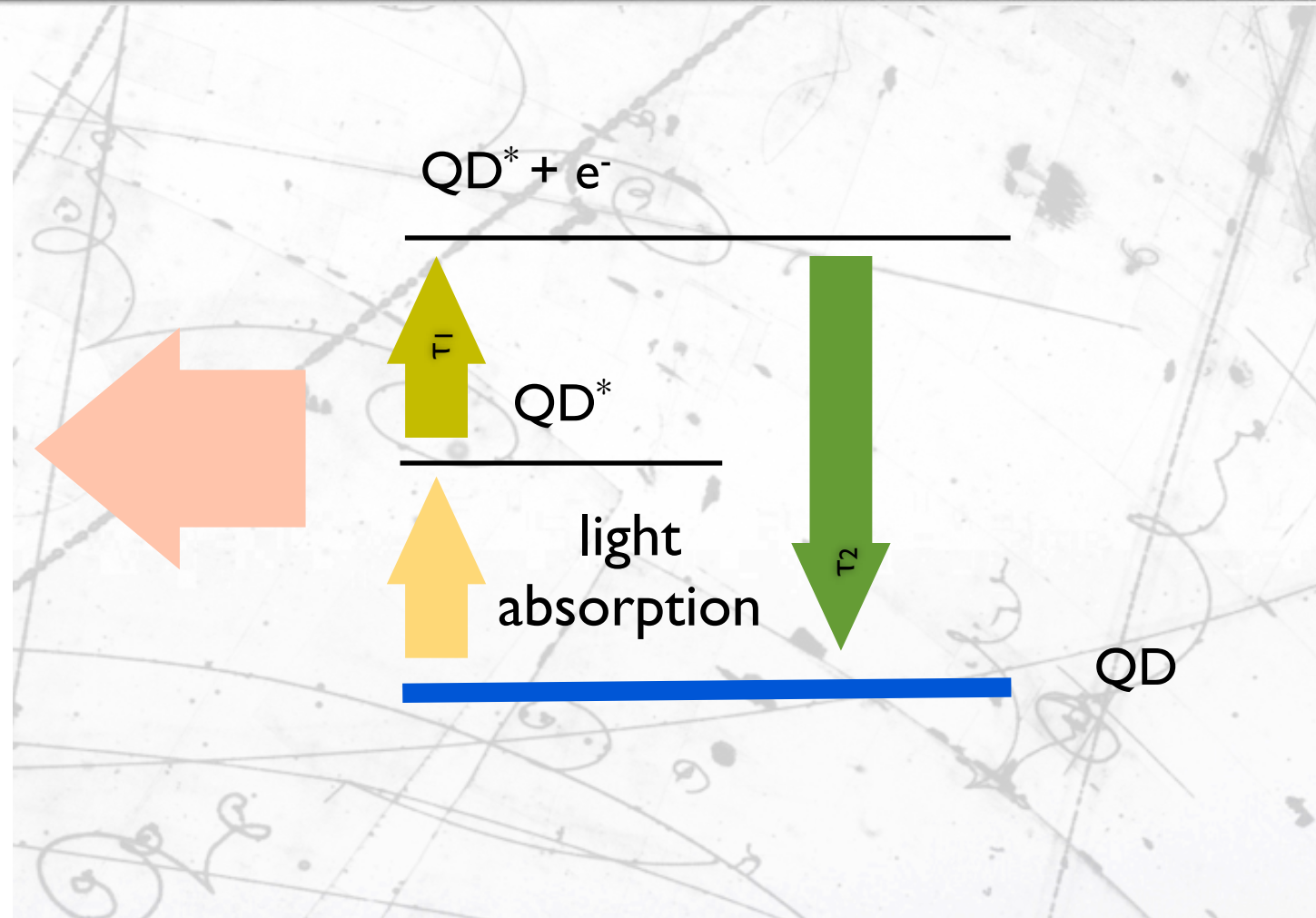
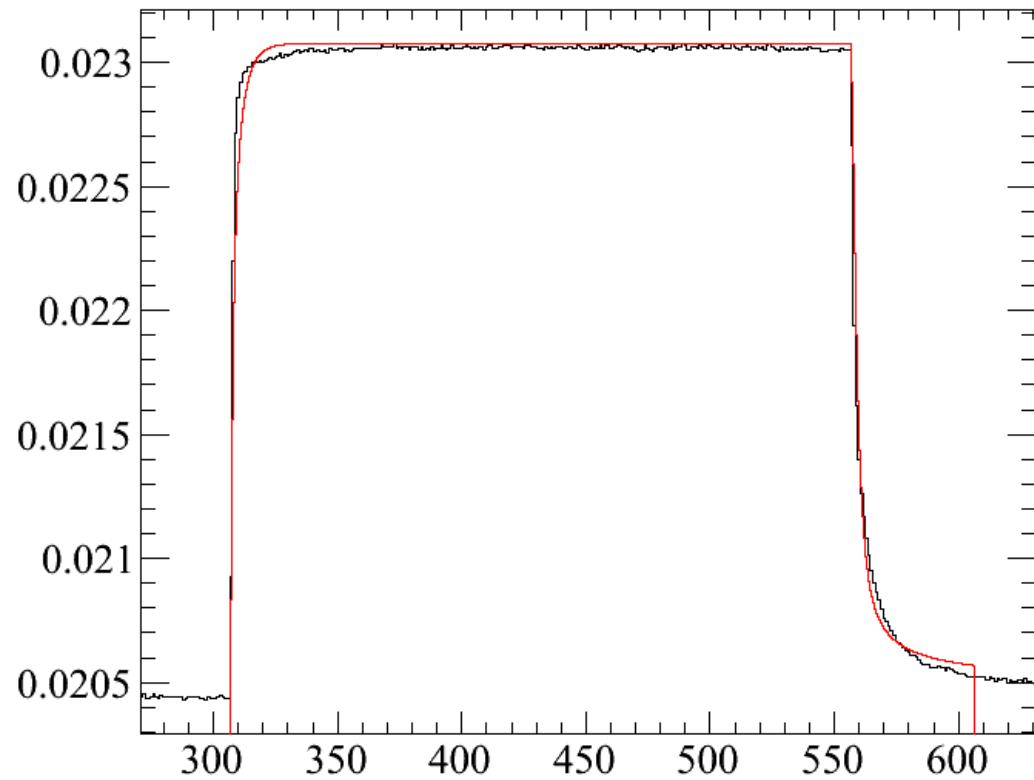







- Trying to understand the response shape.
- This is important to understand the dynamics of the photosensors → keep trying!



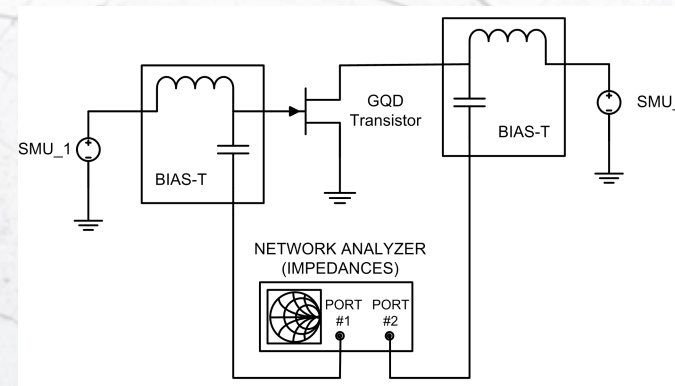
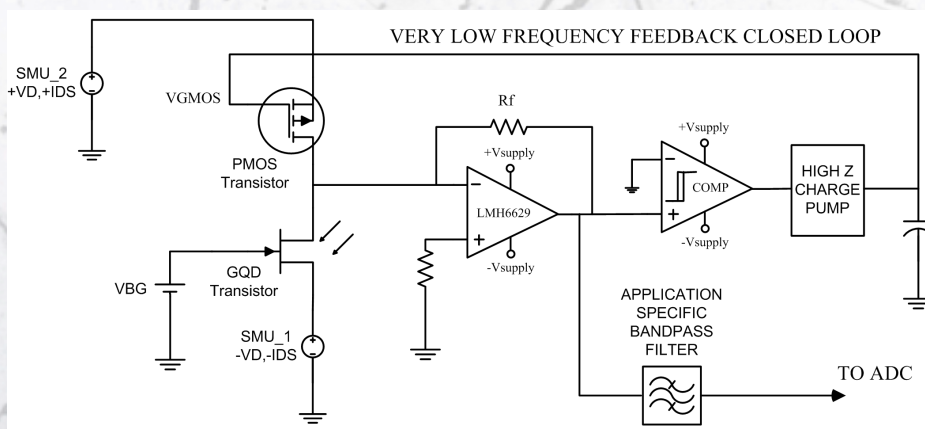
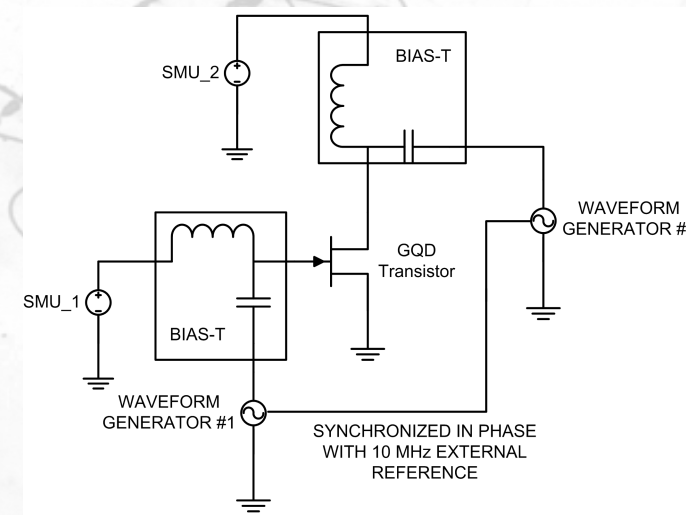
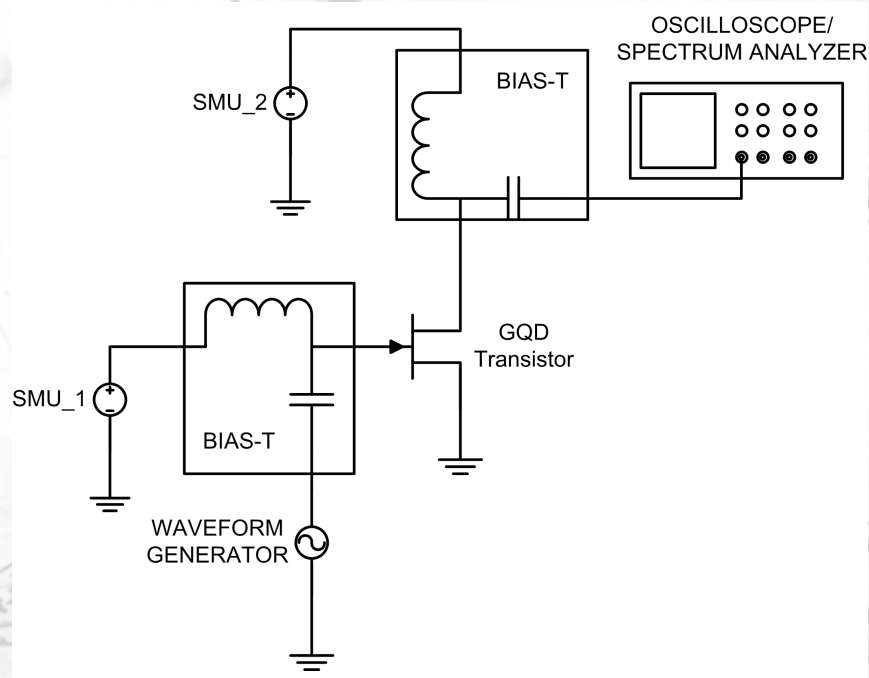


- Another alternative model:
  - The transition probability is function of the separation of the energy level and occupancy.
  - With a  $\tau_{1,2} = f(N_{QD^* + e^-})$



- The main problem of graphene readout is that it is pure resistive: there is always a continuous current through the device.
- How to read the graphene reducing the total current?:
  - pulsing/sampling the readout. 
  - reducing the  $V_{DS}$  to the minimum (noise?).
  - Sinusoidal  $V_{DS}$  so the integral of current = 0.
  - Compensating the current.







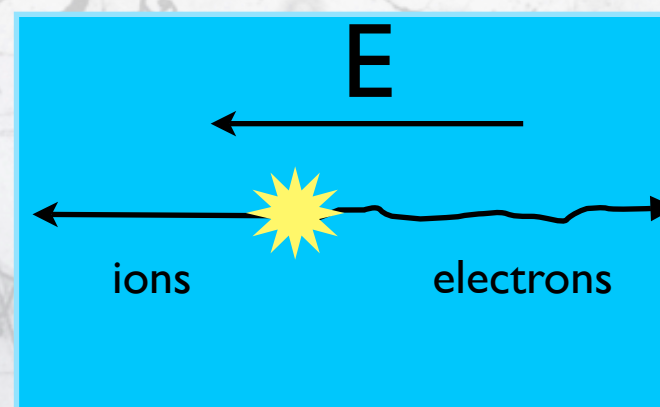
- The project is getting momentum.
- Two weeks ago we posted proposal to the EU FP7 graphene flagship to develop a readout ASIC for an array of 64x64 pixels for an infrared camera.
- The project is supported by ICFO but they could not participate to be already part of the graphene flagship.
- Three partners:

**GIMAGING**



- This collaboration allows us to get hands into the technology but we want to go further:
  - applications in HEP as photosensors:
    - cheap to produce
    - large area coverage,
    - tuning of wavelengt, check options for UV and DUV for noble gas scintillator.
  - IFAE neutrino is interested in investigating the possibility of detecting ions from a TPC ionization: ions act as quantum dots or excite quantum dots.
  - Precise positioning, small attachment, no gain needed, ...

Graphene  
TPC ?



traditional  
TPC



# Final remarks



- This is not the only concept of graphene photosensor, actually the readout for GImaging should probably adapt to the other options.
- We are starting to look into these devices:
  - A lot of fun!
  - We are just at the beginning of understanding them and exploring possible applications.
  - We would like to share the developments with the IFAE to explore possible synergies with other groups.







# Additional slides



# Dispersion relation

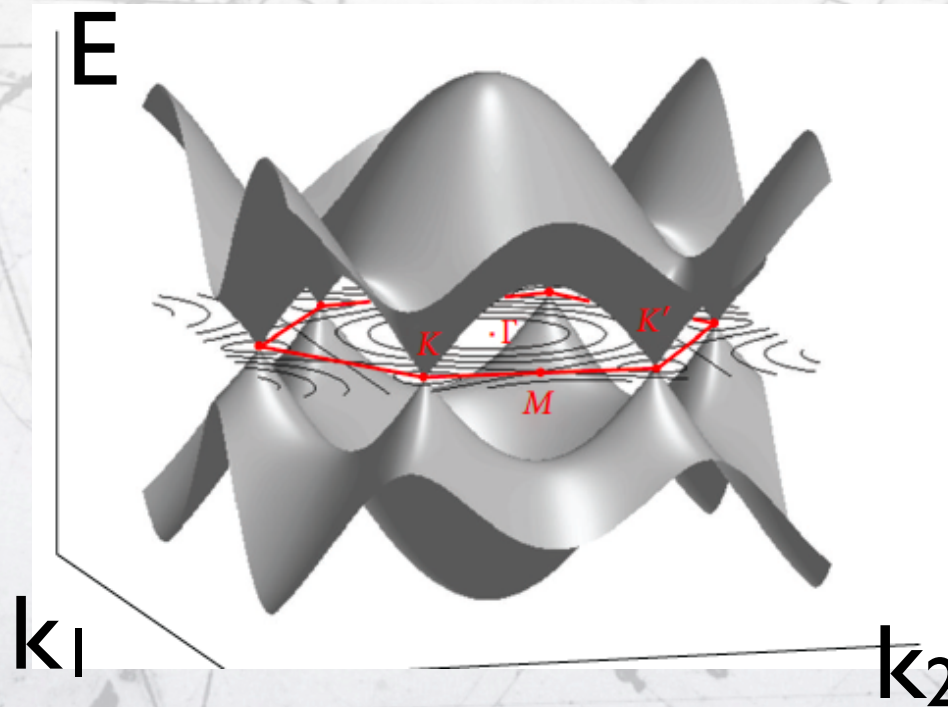
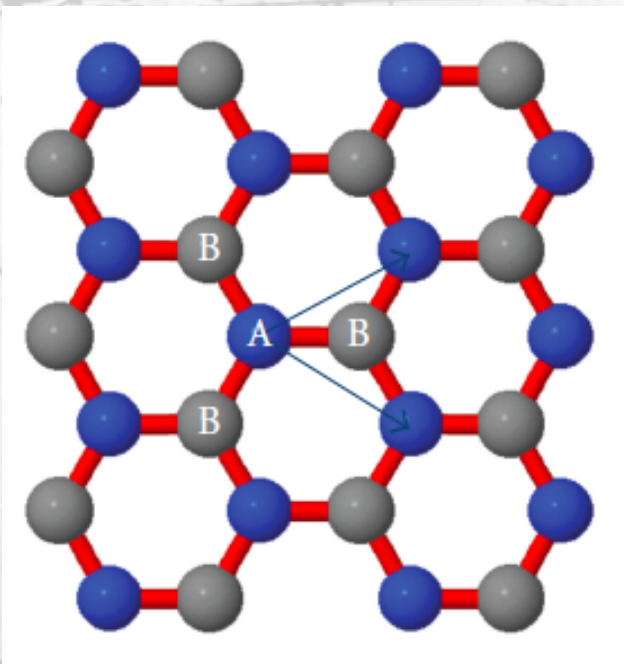


$$H_{\vec{k}} = \begin{pmatrix} 0 & 2.7e^{i\vec{k}\vec{a}_1} + 2.7e^{i\vec{k}\vec{a}_2} + 2.7e^{i\vec{k}\vec{a}_3} \\ 2.7e^{-i\vec{k}\vec{a}_1} + 2.7e^{-i\vec{k}\vec{a}_2} + 2.7e^{-i\vec{k}\vec{a}_3} & 0 \end{pmatrix}$$

$$\vec{a}_1 = (1, 0)$$

$$\vec{a}_2 = (-1/2, \sin \pi/3)$$

$$\vec{a}_3 = (-1/2, -\sin \pi/3)$$



Dirac points are the connection between valence (lower surface) and conduction bands (higher surface).

